M agnetization-dependent T_c shift in F/S/F trilayers with a strong ferrom agnet

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W e have m easured the superconducting transition temperature T_c of N i/N b/N itrilayers when the m agnetizations of the two outer N i layers are parallel (P) and antiparallel (A P). The largest di erence in T_c occurs when the N b thickness is just above the critical thickness at which superconductivity disappears completely. W e have observed a di erence in T_c between the P and A P states as large as 41 m K - a signi cant increase over earlier results in sam ples with higher T_c and with a C uN i alloy in place of the N i. O ur result also dem onstrates that strong elemental ferrom agnets are prom ising candidates for future investigations of ferrom agnet/superconductor heterostructures.

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Heterostructures composed of ferrom agnetic (F) and superconducting (S) m aterials have attracted m uch theoretical and experim ental attention due to the rich physics produced by the interplay between competing symmetries of the order parameters [1]. In an S/F bilayer the exchange eld of the ferrom agnet m odulates the superconducting order param eter as it decays inside the ferrom agnet over a very short distance. K ontos et al. [2] used tunneling spectroscopy to observe the dam ped oscillations of the order param eter by m easuring the density of states (DOS) for di erent thickness ferrom agnets. R yazanov et al. [3] observed -state Josephson coupling in an S/F/S trilayer rst by varying tem perature, then later by varying the thickness of the ferrom agnet [4]. Earlier, several groups [5, 6, 7] had observed oscillations in the critical tem perature T_c of S/F bilayers as a function of the ferrom agnet thickness d_F . Under ideal conditions T_c oscillations arise from interference between the transm itted superconducting wave function through the S/F interface and the wave re ected from the opposite surface of the ferrom agnet, although in some cases alternative explanations have been proposed [8]. In many experim ents, weakly ferrom agnetic alloys were used in order to reduce the size of the exchange splitting in the conduction band, E_{ex} , and thus increase the penetration length F for C opper pairs, where $F = -v_F = 2E_{ex}$ in the clean lim it and v_F is the Ferm i velocity of the ferrom agnet [9].

A n alternative way to probe the in uence of a ferrom agnet on a superconductor is to look for T_c variations in an F/S/F trilayer structure based on the mutual orientation of the two ferrom agnet magnetizations [10, 11]. This e ect was observed [12] and later reproduced [13] in a Cu₁ x N i_x /N b/Cu₁ x N i_x system, where a weak ferrom agnet was used because it is "less devastating to superconductivity." The largest di erence in T_c observed between the antiparallel (AP) and parallel (P) states of the F-layer mutual magnetizations was only 6 m K when T_c was 2.8 K. U nlike other experiments [2, 3, 4, 5, 6, 7] that require the ferrom agnet thickness to be comparable to F, however, a positive feature of this experiment is that the T_c di erence is predicted to persist even for thick

F layers [10, 11]. Thus it proves advantageous in studying systems with strong elemental ferrom agnets, which have extrem ely short values of $_{\rm F}$.

Experim ental studies of F/S system s with strong ferrom agnets are of interest because they provide new challenges to theory, which does not yet address the full com plexity of the ferrom agnetic state with its di erent DOS and v_F of the majority and minority spin bands. Furtherm ore, pure elem ental ferrom agnets are in the clean $\lim it$, F < F where F is the mean free path; this com plicates use of the the popular U sadel equations norm ally applied to the dirty lim it. We are motivated to work in the limit of thick ferrom agnetic layers, in anticipation of future situations where superconducting order with spin-triplet sym m etry is induced in a superconductor surrounded by ferrom agnets with noncollinear m agnetizations [14]. (W hen d_F $_{\rm F}$, the singlet component of the order parameter is completely damped.) Lastly, we wish to understand whether, in an F/S/F system with a strong ferrom agnet, a large di erence in T_c between the P and AP states can be achieved, as envisioned in the proposals for a superconducting spin switch [10, 11]. The Ni/Nb system has been shown to be a viable candidate for experiments on F/S systems [15, 16]. In this paper we will show that N i/N b/N itrilayers exhibit a signi cant T_c shift depending on the mutual orientation of the magnetizations of the two Nilayers.

Sets of N i(7)/N b (d_s)/N i(7)/Fe₅₀M n₅₀ (8)/N b (2) m ultilayers (all thicknesses are in nm) were directly deposited onto Si substrates by magnetically-enhanced triode dc sputtering in a high vacuum chamber with a base pressure in the low 10⁸ Torr and an A rpressure of 2.0 1^d Torr. The N i thickness of 7 nm was chosen to be much longer than _F, which we estimate to be 0.8 nm using $2E_{ex} = 0.23$ eV and $v_F = 0.28$ 1^f0m /s for the majority band [17]. The purpose of the FeM n is to pin the magnetization direction of the top N i layer by exchange bias [18]. The non-superconducting N b capping layer protects the FeM n from oxidation. A fler deposition, the sam ples were heated to 180 C under vacuum, just above the blocking tem perature of FeM n, and cooled in an ap-

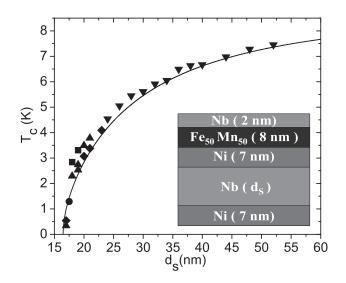


FIG. 1: Critical temperature vs. Nb thickness for Ni(7)/Nb(d_s)/Ni(7)/Fe₅₀M n₅₀ (8)/Nb(2) samples (all thicknesses are in nm). Dierent symbols represent dierent sputtering runs. The solid line represents the theoretical t. Inset: Schem atic cross-section of the samples.

plied eld of 2000 e in the plane of the multilayer. This procedure pins the top N i layer while leaving the bottom N i layer free to rotate in a sm all applied magnetic eld.

Four-probe resistance m easurements with the current in the plane of the multilayer were performed to determine $T_{\rm c}$. Samples had lateral dimensions 4.3 mm \times 1.6 mm. The $T_{\rm c}$ of each sample was dened to be the temperature at which the resistance dropped to half its normal state value. Fig. 1 shows the results for $T_{\rm c}$ measurements for samples from several sputtering runs, where $d_{\rm s}$ was varied between 16-52 nm . $T_{\rm c}$ shows a strong dependence on the superconductor thickness close to a critical thickness, $d_{\rm s}^{\rm cr}$, where the sensitivity to ferrom agnetism is enhanced. There is no superconductivity above 36 mK for $d_{\rm s} < d_{\rm s}^{\rm cr}$ 16.5 nm.

The magnetic con guration of our structures was veried on simultaneously sputtered samples of larger lateral size, in a SQUID magnetometer. Fig. 2 shows a plot of magnetization vs. applied eld H for a sample with d = 18 nm taken at 100 K. The narrow hysteresis loop near H = 0 shows the switching behavior of the free Nilayerwith a coercive eld $H_c = 350 \text{ e. T}$ hew ider loop shows switching of the pinned layer and is shifted to nonzero H due to the exchange bias between the top Nilayer and the FeM n. Applied elds of 1000 e switch the spin-valve between the P and AP con gurations. The nearly zero net m agnetization observed at -100 O e indicates very good AP alignm ent between the pinned and free Ni layers, while the nearly saturated m agnetization observed at + 100 O e indicates good P alignm ent. Sim ilarly good alignm ent of the P and A P states can be achieved at low tem perature. The inset to Fig. 2 shows a minor hysteresis loop with

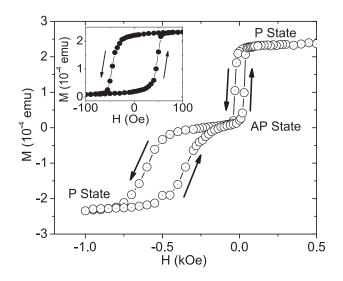


FIG.2: Magnetization vs. applied eld for a $d_s = 18$ nm sample measured at T = 100 K.At 50 O e the free bottom N i layer switches while the pinned top N i layer switches at -500 O e. Inset: minor loop measured at T = 2.29 K showing the switching of the free N i layer.

H $_{\rm c}$ 50 O e taken at 2.29 K, which corresponds to the middle of the superconducting transition for this sam ple. W e obtain the same behavior for tem peratures above and below the transition tem perature.

M easurem ents of T_c^P and T_c^{AP} were performed by alternating the applied eld between + 100 and -100 0 e, as the tem perature was slow ly decreased through the transition region. The largest shift in critical temperature, T_C^{A P} T_c^P , should occur in samples with the N b T_{c} thickness close to d_s^{cr} . Fig. 3 shows a plot of R vs. T for a sample with $d_s = 17 \text{ nm}$, measured in a dilution refrigerator. Two distinct transitions are observed for P and AP alignment, with a separation in temperature 28 mK . A second sample with $d_s = 17 \text{ nm}$ showed $T_{\rm C}$ 41 mK, but with a slightly broader transition а $T_{\rm C}$ centered at 0.34 K.Sam ples with $d_s = 18 \text{ nm}$ and T_c between 2 and 3 K exhibit values of $\rm ~T_{c}$ of only a few mK, sim ilar to the CuN i/N b/CuN i sam ples m easured previously [12, 13].

The inset to Fig. 3 shows a plot of R vs. H for the rst $d_i = 17$ nm sample at a temperature in the middle of the transition (0.51 K). The data clearly show wellestablished P and AP states at 100 0 e, respectively, with a di erence in resistance of 1.5 . Above the transition the resistance does not change perceptibly when switching from P to AP alignment. An interesting feature of the R vs. H curve is the behavior of the resistance as the eld is swept down from + 150 0 e towards -50 0 e and as the eld is swept up from -150 0 e towards + 50 0 e. In both cases the resistance increases to a value higher than that of the P state after the eld passes through zero. We believe this behavior involves the breaking of

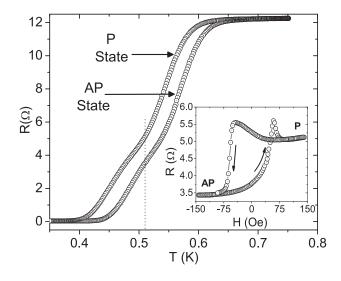


FIG.3: Resistance vs. temperature for the P and AP states of a $d_s = 17$ nm sample measured in 100 Oe. Two distinct transitions are observed, with T $_c = 28$ mK. Inset: Resistance vs. applied eld at T = 0.51 K (dotted line in main graph).

the free ferror agnetic layer into dom ains when H H_c . The dom ain-wall fringe elds penetrate the superconductor, thus suppressing T_c slightly and producing a higher resistance. Note that this e ect is opposite to that observed by other groups [19, 20], where inhom ogeneous magnetization led to enhanced superconductivity in F/S bilayers. In those experiments, the dom ain size must be smaller than the superconducting coherence length so that the C ooper pairs sample multiple dom ains [21], and the magnetic eld penetrating into the superconductor must be small.

The critical tem perature of F/S/F trilayers in the P and AP states has been calculated theoretically by several groups [10, 11, 22, 23, 24]. Since m any experim ents em ploy ferrom agnetic alloys, the usual approach involves solving the U sadel equations in the dirty lim it for both the superconductor and the ferrom agnet. (The dirty lim it applies to S when $l_{s} < _{BCS} = -v_{S} = ^{2}k_{B}T_{c0}$, and to F when $l_{\!_{\rm F}} < ~_{\!_{\rm F}}$, where $l_{\!_{\rm S}}$ and $l_{\!_{\rm F}}$ are the electron m ean free paths in S and F , and T_{c0} is the transition tem perature of the bulk superconductor.) In our case, how ever, the ferrom agnetic m etal is both pure and strong, thus in the clean $\lim it l_F > F$. Hence we use the theory of [11] asmodi ed in section 3,2 of [25] to make it more appropriate for the clean lim it. This theory does not, how ever, incorporate a full description of the majority and minority spin bands of a strong ferrom agnet, with di erent DOS, v_F , and transmission coe cients. The expression for the norm alized critical tem perature of the trilayer is

$$\ln t_c + Re = \frac{1}{2} + \frac{2^2}{t_c (d_s = s)^2} = \frac{1}{2} = 0;$$
 (1)

where $t_c = T_c = T_{c0}$ and T_{c0} is the critical temperature of an isolated Nb lm of the same thickness as the one in the trilayer. The function is determined from the condition tan = R for the P state or (tan R^0) (R^0 tan +) (R^0)²tan = 0 for the AP state, where the complex function $R = R^0 + iR^0$ is given by:

$$R = \frac{d_{s}}{s} \frac{N_{F} v_{F} s}{2N_{s} D_{s}} \frac{1}{1 i_{F} = l_{F}} + 2 = T_{F}}$$
(2)

Eq. (2) is valid when the ferrom agnets are thick enough so that the tanh functions in [25] can be set to 1. This assumption is validated by data on Nb/Nibilayers [16] where oscillations in $T_c (d_F)$ are completely damped for $d_F > 4$ nm. The dimensionless parameters that enter into this theory are the ratios $d_s = s$, $_F = l_F$, the S/F interface transparency T_F , and the combination N $_F v_F \ _S = 2N \ _S D \ _S \ .$ N $_F$ and N $_S$ are the densities of states at the Ferm ienergy of the F and S layers, v_F is the Ferm i velocity of the ferrom agnet, and D $_S$ is the di usion constant of the superconductor.

To avoid thing the data with four free parameters, we follow the strategy outlined by Lazar et al. [8] and by Sidorenko et al. [16]. We determ ine the superconducting coherence length, $_{\rm S}$, from measurements of the critical eld vs. temperature of isolated Nb lm s, with the magnetic eld applied perpendicular to the lm plane. For

In s in the thickness range 20-50 nm, the values of s are close to 6 nm, which we use for our ts [26]. From the asymptotic form of Eq. (1) as t_c ! 0, one nds 2 $^2 = (d_s^{cr} = s)^2 = 1=4$, where = 1:781. Substituting d_s^{cr} 16.5 nm and using Eq. (2) (while ignoring the sm all im aginary term), we obtain the constraint

$$\frac{N_{F} V_{F} s}{2N_{S} D_{S} (d_{s}^{cr})} \frac{1}{1 + 2 = T_{F}} \qquad \frac{cr tan cr}{(d_{s}^{cr} = s)} = 0.24$$
(3)

Estimates of the product $N_F v_F$ vary substantially in the literature. From [27] and [17], we obtain respectively $10^{40} \text{ J}^{1} \text{ m}^{3}$ and $v_{\text{F}} = 0.28$ $N_{\rm F} = 1:77$ 10 m /s. Fierz et al. [28], how ever, quote $_{\rm F}$ $l_{\rm F}$ = 0:7 2:3 f m² for Ni, which when combined with the Einstein relation $1 = F_{\rm F} = N_{\rm F} v_{\rm F} e^2 = 3$ in ply values 3-10 times smaller for $N_F v_F$. Combining these values with $N_S = 5:31$ 140 J 1 m 3 [29] and using our measured D $_{\rm S}$ (d $_{\rm s}^{\rm cr}$) = 2.8 10⁴ m²/s, we obtain $T_F = 0.05$ 0.6. The bulk resistivity of our sputtered N i lm sat 4.2 K is $_F = 33 n m$, which leads to values of $l_{\rm F}$ between 7 and 70 nm, given the range in Fly quoted above. Since the Niused in our trilayers is thin, 1/ is probably limited by surface scattering, so we use the lower estimate $l_{r} = 7 \text{ nm}$, hence 0.1. In fact, the t to $T(d_s)$ is quite insensitive $_{\rm F} = \mathbf{l}_{\rm F}$ to the values of T_F and $_F=l_F$. We used $_F=l_F$ = 0:1 and $T_F = 0.3$ to obtain the curve shown in Fig. 1, which ts the data rem arkably well.

A more stringent test of the theory is the prediction of T_c , which depends sensitively on both T_F and $_F = l_F$.

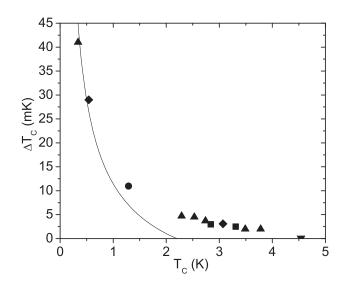


FIG. 4: Symbols: T $_{\rm c}$ vs. T $_{\rm c}$ for our 11 thinnest samples. The line represents a tusing $_{\rm F}$ =L $_{\rm F}$ = 0:7 and T $_{\rm F}$ = 1:0, values larger than our best estimates.

Thickness deviations from nom inal values produce scatter in plots of $T_{\rm c}$ or $~~T_{\rm c}$ vs. $d_{\rm s}$, therefore Fig. 4 shows a plot of T_c versus T_c . If we calculate T_c using our best estim ate of $_{F} = l_{F}$ and the upper lim it of T_{F} given above, the maximum value of T_c is only a few mK when T_c is well below 1 K { hardly visible on Fig. 4. If we relax the constraints we have placed on the parameters, and instead try to produce the best t to the $T_{c}(d_{s})$ data, we nd that a reasonable t can be obtained when $_{\rm F} = l_{\rm F}$ is allowed to be much larger than our original estimate. Fig. 4 shows a tusing $_{\rm F} = l_{\rm F} = 0.7$ and $T_{\rm F} = 1.0$. Sim ilar curves can be produced by simultaneously varying $_{\rm F} = l_{\rm F}$ and $T_{\rm F}$ while keeping their product nearly constant. Fitting the T_c data requires letting $F = I_F$ exceed our estim ate substantially. Our 1/2 estim ate m ay be too large, because the resistivity is dom inated by the longer of the majority or minority band $\frac{1}{2}$, whereas the F/S proximity e ect depends on the shorter of the two [8]. A shorter ly is also in plied by the observation of com plete dam ping of T_c oscillations in Nb/Nibilayers for $d_F > 4$ nm [16]. Nevertheless, producing a reasonable t to our

 $T_{\rm c}$ data entails either increasing $_{\rm F}$ =1 beyond the clean lim it, or increasing $T_{\rm F}$ beyond our original estim ate.

In conclusion, we have observed a large di erence in T_c between the P and AP m agnetic states of N i/N b/N i trilayers, with $T_c^P < T_c^{AP}$. Recently, Ruzanov et al. [30] reported a T_c di erence between the P and AP states of a N $i_{0.8}Fe_{0.2}$ /N b/N $i_{0.8}Fe_{0.2}$ trilayer, but with $T_c^P > T_c^{AP}$. Understanding these opposing behaviors in F/S system s with strong ferrom agnets will require further experiments, as well as theoretical models able to account for the com plexity of real ferrom agnets [31].

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